

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP  
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**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TTN	AA	5,208,182	5/4/93	Narayan et al.			11/12/91
TTN	AB	5,252,173	10/12/93	Inoue			11/22/91
TTN	AC	5,279,687	01/18/94	Tuppen et al.			02/27/90
TTN	AD	6,117,750	09/12/00	Bensahel et al.			12/21/98
TTN	AE	5,210,052	05/11/93	Takasaki			05/13/92
TTN	AF	5,221,413	06/22/93	Brasen et al.			04/24/91
TTN	AG	5,308,444	05/03/94	Fitzgerald, Jr. et al.			05/28/93
TTN	AH	5,442,205	08/15/95	Brasen et al.			09/09/93
TTN	AI	5,810,924	09/22/98	Legoues et al.			06/07/95
TTN	AJ	6,107,653	08/22/00	Fitzgerald			06/23/98

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
TTN	AK	63073398 ✓	3/29/88	Japan			yes (abstract)
	AL						
	AM						
	AN						
	AO						

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
TTN	AP ✓	"Relaxed Ge <sub>x</sub> Si <sub>1-x</sub> structures for III-V integration with Si and high mobility two-dimensional electron gases in Si"; by Fitzgerald et al. 1992 American Vacuum society; pages 1807-1819
TTN	AQ ✓	"GeSi/Si NANOSTRUCTURES" by E.A. Fitzgerald; Department of Materials Science, Massachusetts Institute of Technology (1995) pgs; 1-15

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**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TTN	AA 4,900,372	02/13/1990	Lee et al.	148	33.4	03/02/1989
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					
	AJ					

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	AM					
	AN					
	AO					

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
TTN	AP	Hsin-Chiao Luan et al., "High-quality Ge epilayers on Si with low threading-dislocation densities," <i>Applied Physics Letters</i> , American Institute of Physics, New York, Vol. 75, No. 19, November 8, 1999, pages 2909-2911.
	AQ	

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